

NCE N-Channel Enhancement Mode Power MOSFET

Description

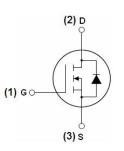
The NCE0275T uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in automotive applications and a wide variety of other applications.

General Features

- $V_{DSS} = 200V, I_D = 75A$ $R_{DS(ON)} < 22mΩ @ V_{GS} = 10V$
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Automotive applications
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



TO-247-3L top view

100% UIS TESTED! 100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0275T	NCE0275T	TO-247-3L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDSS	200	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	75	Α
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	53	Α
Pulsed Drain Current (Note 1)	I _{DM}	300	А
Maximum Power Dissipation	P _D	360	W
Derating factor		2.4	W/℃
Single pulse avalanche energy (Note 3)	Eas	600	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance Junction-to-Case (Note 1)	Rose	0.42	°C/W
Thermal Resistance, Junction-to-Case (Note 1)	K θJC	0.42	[C/ vv [



Electrical Characteristics (T_C=25 [°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•	•		
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	200	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =200V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics	•					
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =40A	-	19	22	mΩ
Forward Transconductance	g FS	V _{DS} =20V,I _D =40A	-	115	-	S
Dynamic Characteristics			•			
Input Capacitance	C _{lss}), (20)(), (2)	-	8238	-	PF
Output Capacitance	Coss	V _{DS} =100V,V _{GS} =0V,	-	275	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	112	-	PF
Switching Characteristics	•					
Turn-on Delay Time	t _{d(on)}		-	17	-	nS
Turn-on Rise Time	t _r	V _{DD} =100V,I _D =40A,	-	18	-	nS
Turn-Off Delay Time	t _{d(off)}			56	-	nS
Turn-Off Fall Time	t _f		-	22	-	nS
Total Gate Charge	Qg		-	152.7	-	nC
Gate-Source Charge	Q _{gs}	ID=40A,VDD=100V,VGS=10V	-	44.5	-	nC
Gate-Drain Charge	Q _{gd}		-	47.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	VsD	V _{GS} =0V,I _S =75A	-	-	1.2	V
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 40A	-	136	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/μs ^(Note2)	-	458	-	nC

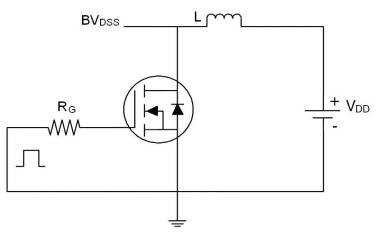
Notes:

- 1. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 2. Pulse Test: Pulse Width \leq 400 μ s, Duty Cycle \leq 2%.
- 3. EAS condition: Tj=25 $^{\circ}\!\!\mathrm{C}\,,V_{DD}\!=\!50V,V_{G}\!=\!10V,L\!=\!1mH,Rg\!=\!25\Omega$

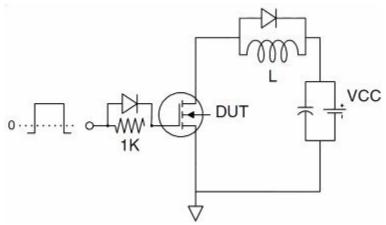


Test Circuit

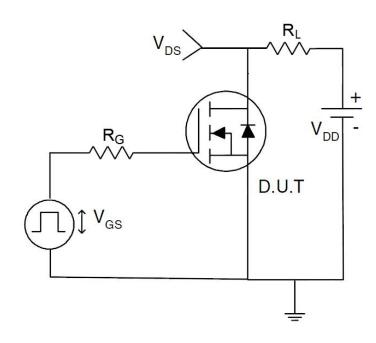
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics(Curves)

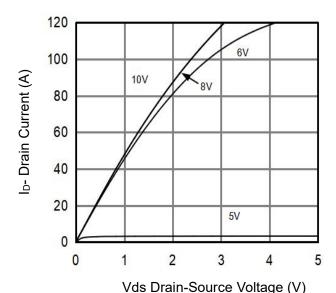
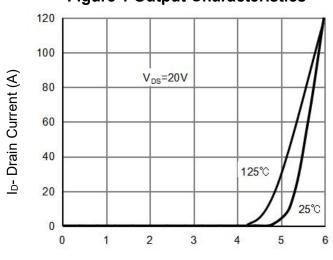


Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

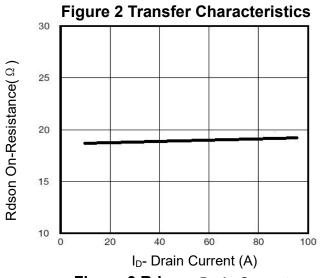
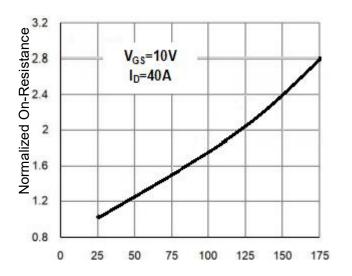


Figure 3 Rdson- Drain Current



T_J-Junction Temperature(°C)

Figure 4 Rdson-JunctionTemperature

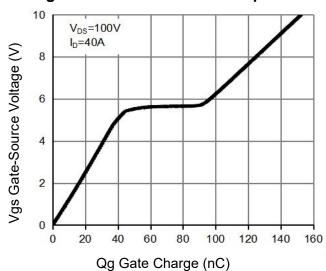


Figure 5 Gate Charge

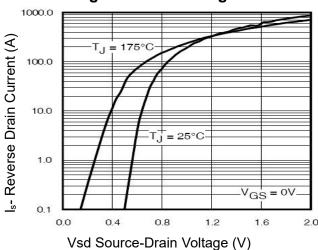


Figure 6 Source- Drain Diode Forward



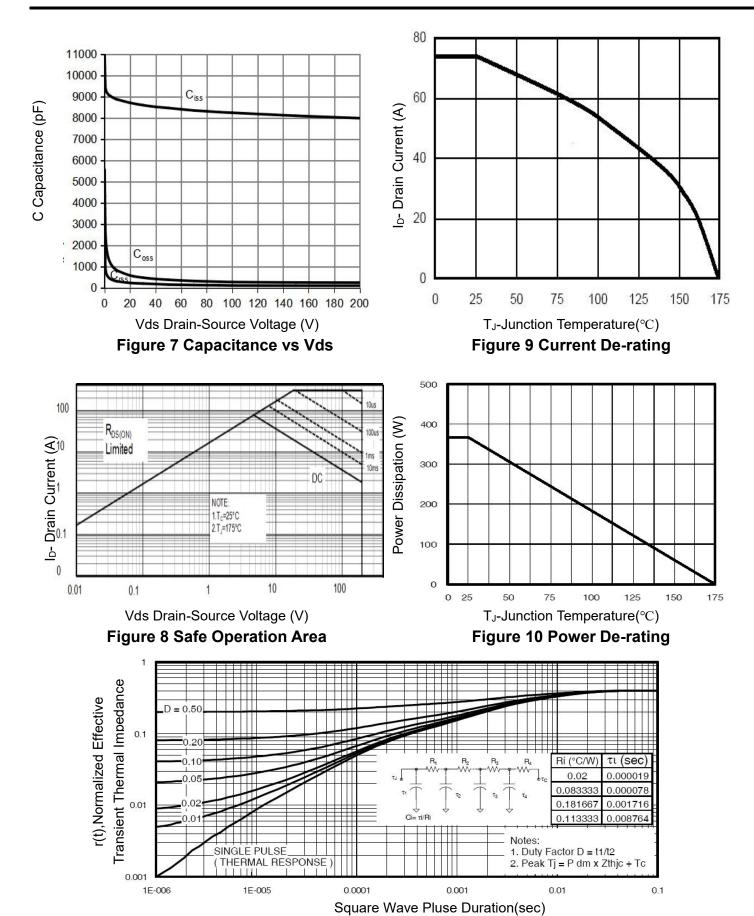
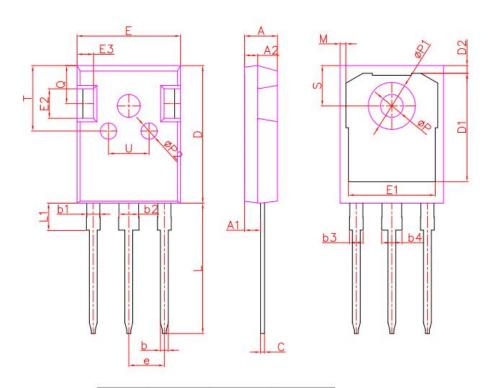


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-247-3L Package Information



		247	
DIM.	MIN.	NOM.	MAX.
Α	4.90	5.00	5.10
A1	2.31	2.432	2.51
A2	1.90	2.00	2.10
b	1.16	1.20	1.26
b1	1.96	2.00	2.06
b2	2.96	3.00	3.06
b3	1-	-	2.25 3.25
b4	1941	-	
С	0.59	0.60	0.66
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.17	1.35
E	15.70	15.80	15.90
E1	13.10	13.26	13.50
E2	4.40	4.50	4.60
E3	2.40	2.50	2.60
е		5.436BSC	
L	19.80	19.90	20.10
L1	-	-	4.30
М	0.35	0.89	0.95
Р	3.40	3.50	3.60
P1	7.00	7.20	7.40
P2	2.40	2.50	2.60
Q	5.60	5.80	6.00
S	6.05	6.15	6.25
T	9.80	10.00	10.20
U	6.00	6.20	6.40



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